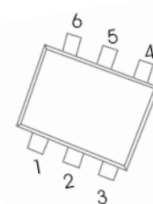
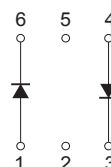


FEATURES

Surface mount schottky barrier diode arrays

Marking: KAV



SOT-563

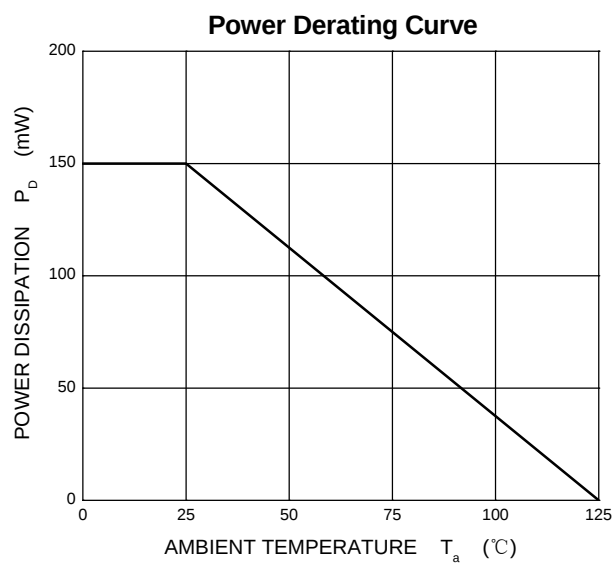
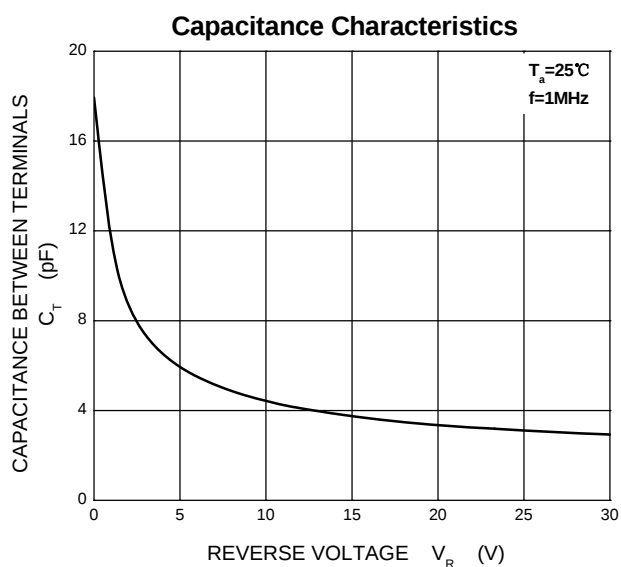
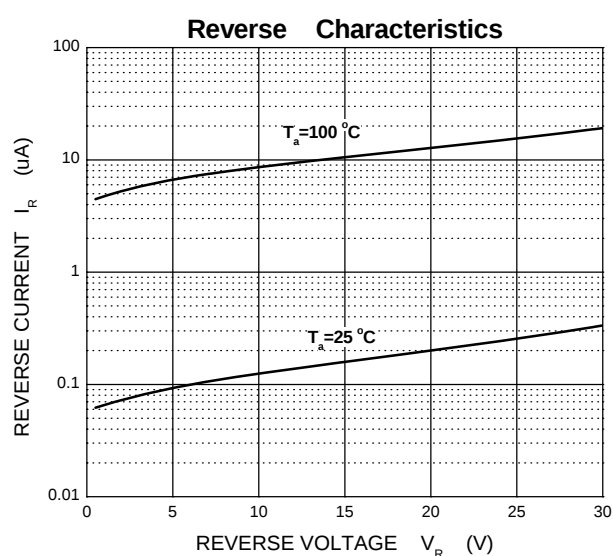
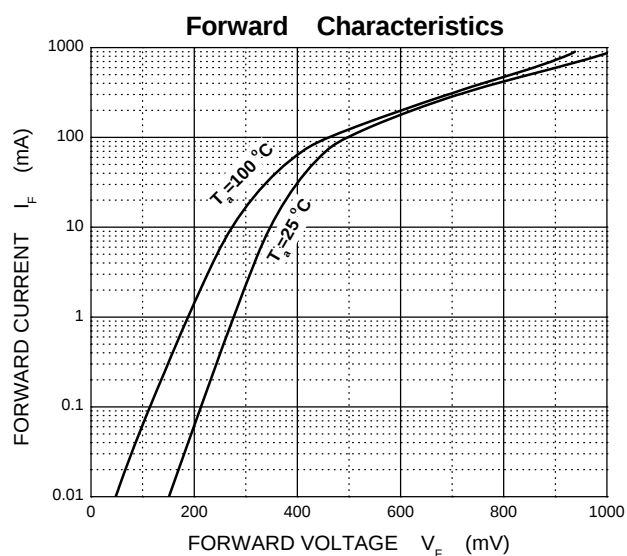
Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking V oltage	V_{RRM} V_{RWM} V_R	30	V
Average Rectified Output Current	I_O	200	mA
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I_{FSM}	600	mA
Repetitive Peak Forward Current @ t≤1s, δ ≤0.5	I_{FRM}	300	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	667	°C/W
Junction Temperature	T_J	125	°C
Storage Temperature	T_{STG}	-65-125	°C

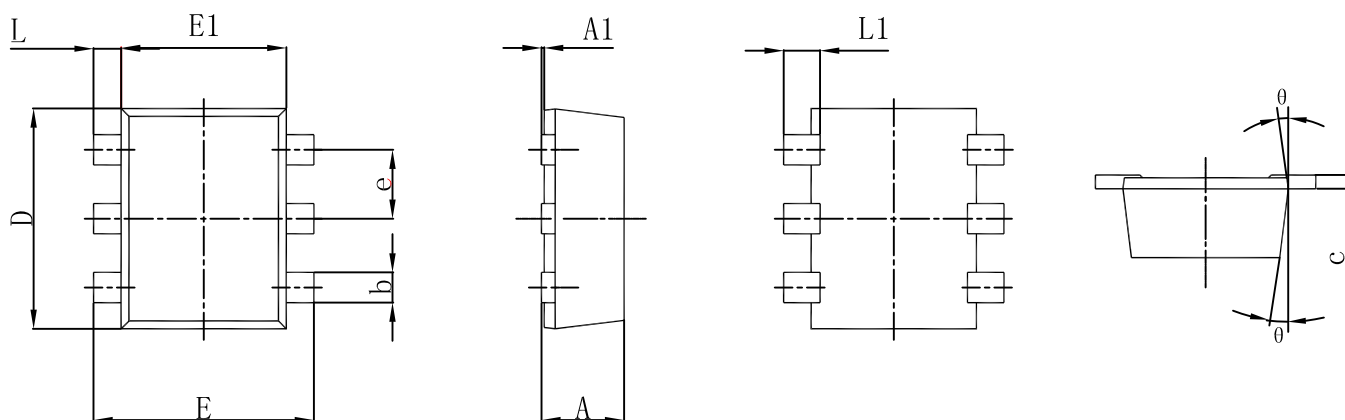
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	30		V
Reverse voltage leakag e current	I_R	$V_R = 25V$		2	uA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 30mA$ $I_F = 100mA$		320 400 500 1000	mV
Total capacitance	C_T	$V_R = 1V, f = 1MHz$		10	pF
Reverse recovery time	t_{rr}	$I_F = 10mA, I_R = 10mA \sim 1mA$ $R_L = 100\Omega$		5	ns

Typical Characteristics

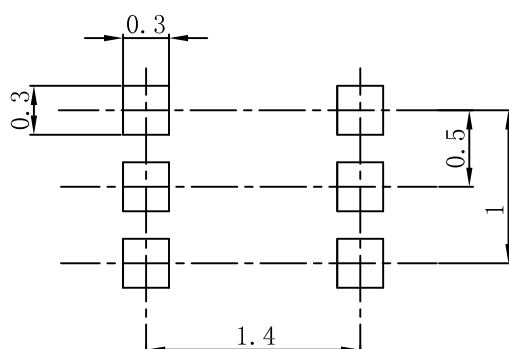


SOT-563 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	7° REF.		7° REF.	

SOT-563 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.